NSN 5961-01-532-4773

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View Online at https://aerobasegroup.com/nsn/5961-01-532-4773 **Inclosure Material:** Plastic or ceramic **Overall Length:** 1.130 inches **Terminal Length:** 0.500 inches **Overall Height:** Between 0.160 inches and 0.190 inches **Overall Width:** 0.039 inches **Function For Which Designed:** Switching **End Application:** Nsn 4935-01-136-0233; shop equipment, guided missile system; w/s; missile, patriot **Internal Configuration:** Field effect Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-220ab **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 60.0 drain to source voltage **Current Rating Per Characteristic:** 30.00 amperes all primaries of standard range **Power Rating Per Characteristic:** 75.0 watts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Special Features:** Tmos v, power field effect transistor; p-channel enhancement-mode silicon gate **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No

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